"HALF-BRIDGE" IGBT

V_{CES} = 1200V
Ic = 200A
$V_{CE(ON)}$ typ. = 3.2V
@ Ic = 200A

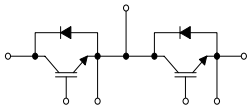
Features

- IGBT NPT Technology
- 10μs Short Circuit Capability
- Low Turn-off losses
- Short tail current
- Positive V_{CE}(on) temperature coefficient

Applications

- AC & DC Motor controls
- General purpose inverters
- Optimized for high current inverter (AC TIG Welding machines)
- Servo Controls
- UPS, Robotics

Package : V3



Absolute Maximum Ratings @ Tj=25℃ (per leg)

Symbol	Parameter	Condition	Ratings	Unit
V_{CES}	Collector-to-Emitter Voltage	V_{GE} = 0V, I_C = 1.0mA	1200	V
V_{GES}	Gate emitter voltage		± 20	V
I_C	Continuous Collector Current	T_C = 70℃ (25℃)	200 (260)	A
I_{CM}	Pulsed collector current	T_C = 70℃ (25℃)	400 (520)	A
I_F	Diode Continuous Forward Current	T_C = 70℃ (25℃)	200 (260)	A
I_{FM}	Diode Maximum Forward Current		520	A
T_{SC}	Short Circuit Withstand Time	T_C = 100℃	10	μs
V_{iso}	Isolation Voltage test	AC 1 minute	2500	V
T_j	Junction Temperature		-40 ~ 150	℃
T_{stg}	Storage Temperature		-40 ~ 125	℃
Weight	Weight of Module		360	g
Mounting Torque	Power Terminal Screw : M5		3.5	Nm
	Terminal connection Screw : M5		3.5	Nm

Electrical Characteristics @ Tj = 25℃ (unless otherwise specified)

Symbol	Parameters	Min	Typ	Max	Unit	Test conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	-	-	V	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	-	3.2	3.5		I_C = 200A, V_{GE} = 15V
$V_{GE(th)}$	Gate Threshold Voltage	4.0	5.0	6.0		V_{CE} = V_{GE}, I_C = 500μA
I_{CES}	Zero Gate Voltage Collector Current	-	-	1.0	mA	V_{GE} = 0V, V_{CE} = 1200V
I_{GES}	Gate-to-Emitter Leakage Current	-	-	±200	nA	V_{CE} = 0V, V_{GE} = ±20V
V_{FM}	Diode Forward Voltage Drop	-	2.4	2.7	V	I_C = 200A

Switching Characteristic @ Tj = 25℃ (unless otherwise specified)

Symbol	Parameters	Min	Typ	Max	Unit	Test conditions
C_{ies}	Input capacitance	-	8600	-	pF	V_{CC} = 30V, V_{GE} = 0V f = 1.0MHz
C_{oss}	Output capacitance	-	790	-		
C_{res}	Reverse transfer capacitance	-	320	-		
$t_{d(on)}$	Turn-on delay time	-	72	94	ns	T_j = 125℃, V_{CC} = 600V I_C = 200A, V_{GE} = 15V R_G = 4.7Ω
t_r	Rise time	-	32	45		
$t_{d(off)}$	Turn-off delay time	-	366	400		
t_f	Fall time	-	45	58		
I_{rr}	Diode Peak Reverse Recovery current	-	50	-	A	T_j = 125℃, V_{CC} = 600V I_F = 120A, V_{GE} = 15V R_G = 4.7Ω
t_{rr}	Diode Reverse Recovery time	-	180	-	ns	

Thermal Characteristic Values

Symbol	Parameters	Min	Typ	Max	Unit
$R_{\Theta JC}$	Junction-to-Case (IGBT Part, Per 1/2 Module)	-	-	0.10	W/℃
$R_{\Theta JC}$	Junction-to-Case (Diode Part, Per 1/2 Module)	-	-	0.20	
$R_{\Theta CS}$	Case-to-Heat Sink (Conductive grease applied)	-	0.04	-	

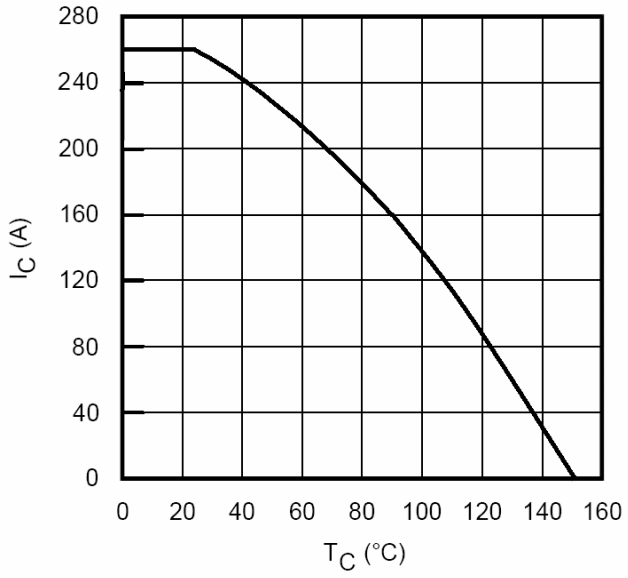


Fig 1. Maximum DC Collector Current vs. Case Temperature

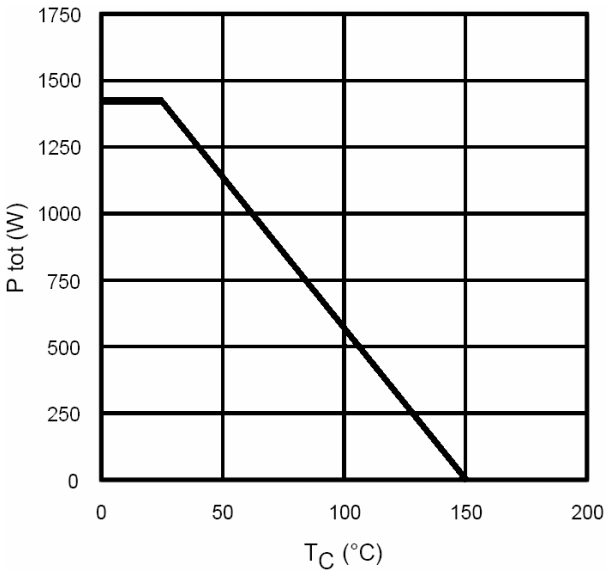


Fig 2. Power Dissipation vs. Case Temperature

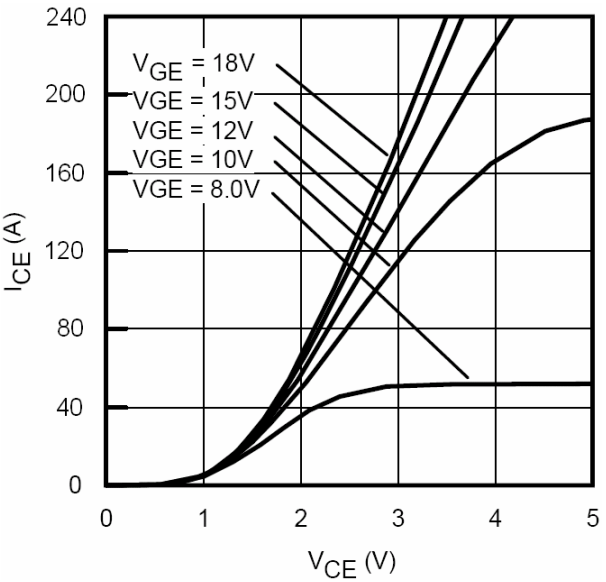


Fig 3. Typ. IGBT Output Characteristics

T_J = 25℃; tp = 80μs

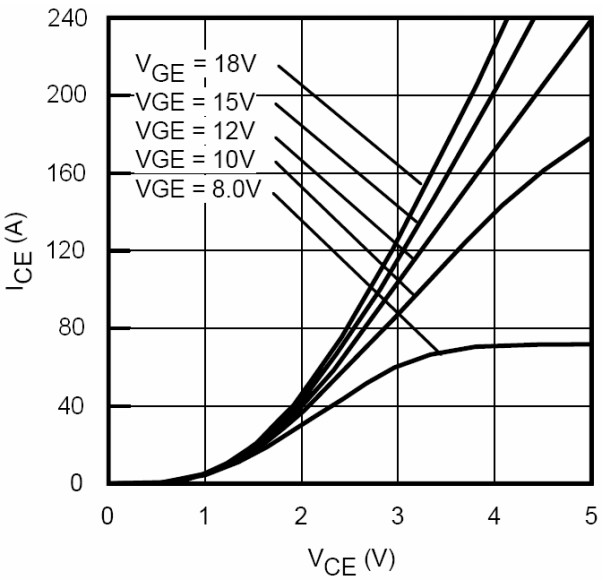


Fig 4. Typ. IGBT Output Characteristics

T_J = 125℃; tp = 80μs

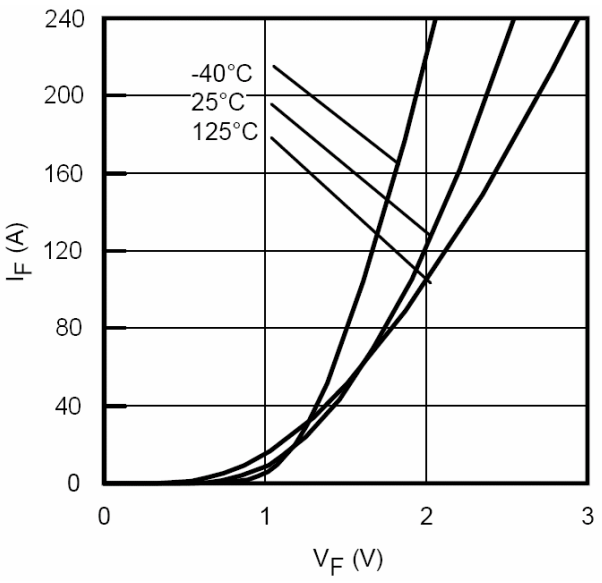


Fig 5. Typ. Diode Forward Characteristics

tp = 80μs

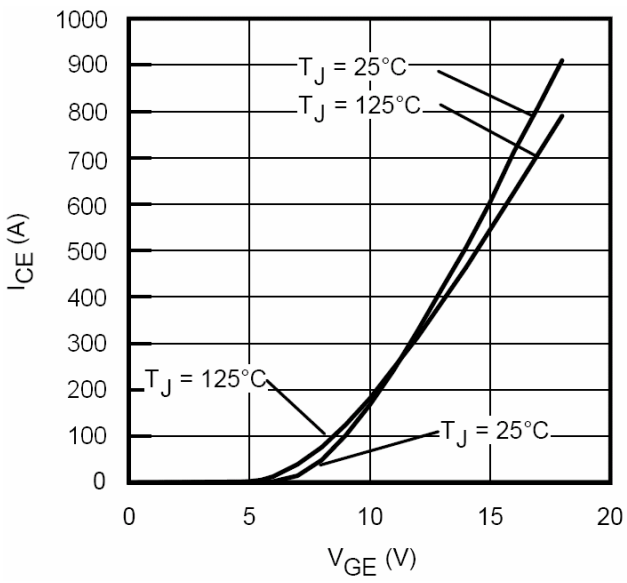


Fig 6. Typ. Transfer Characteristics

V_{CE} = 50V; tp = 10μs

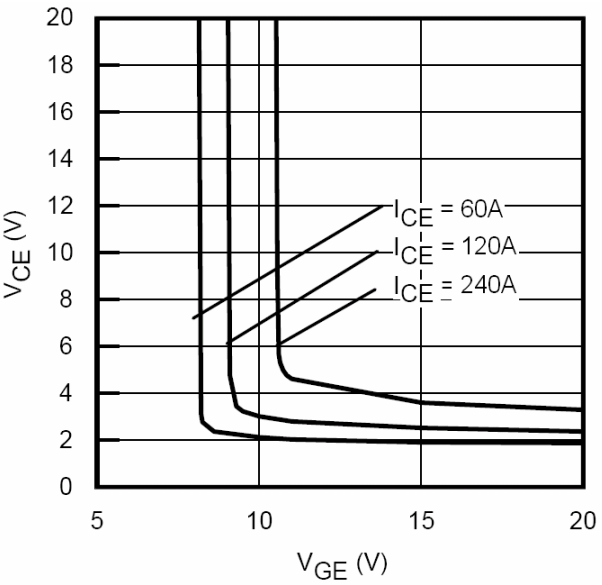


Fig 7. Typical V_{CE} vs. V_{GE}

T_J = 25℃

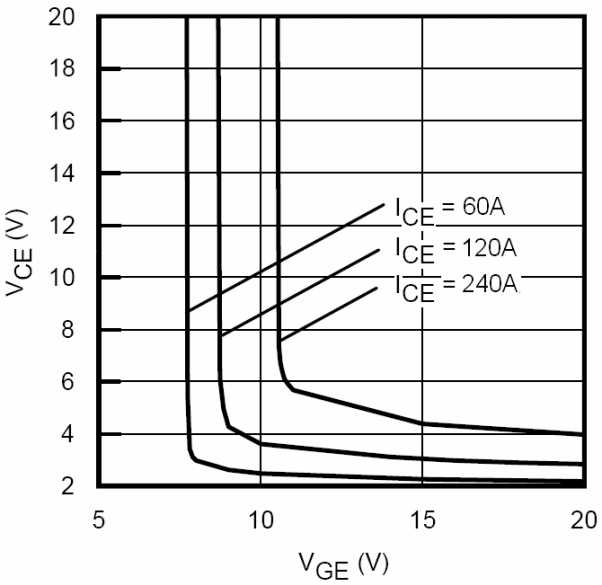


Fig 8. Typical V_{CE} vs. V_{GE}

T_J = 125℃

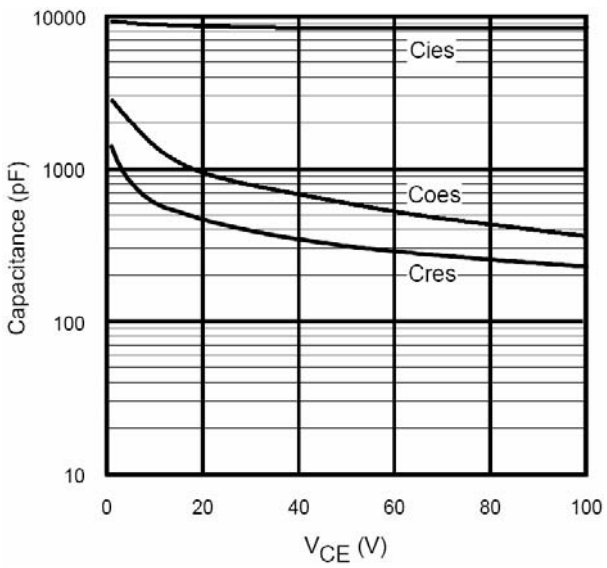


Fig 9. Typ. Capacitance vs. V_{CE}

V_{GE} = 0V; f = 1Mhz

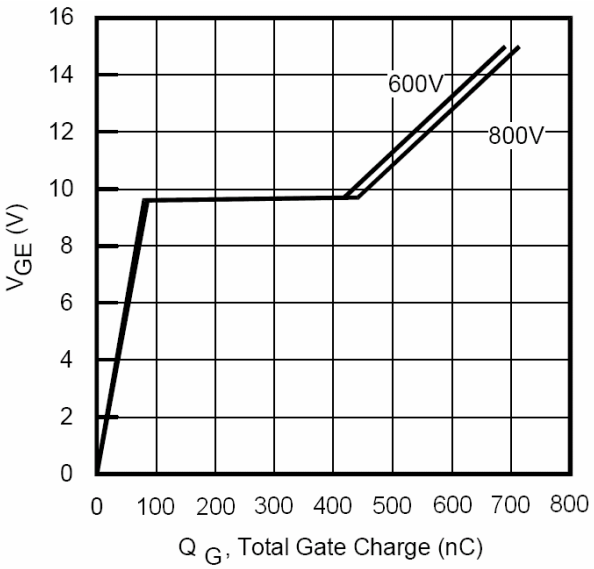


Fig 10. Typical Gate Charge vs. V_{GE}

I_{CE} = 120A; L = 600μH

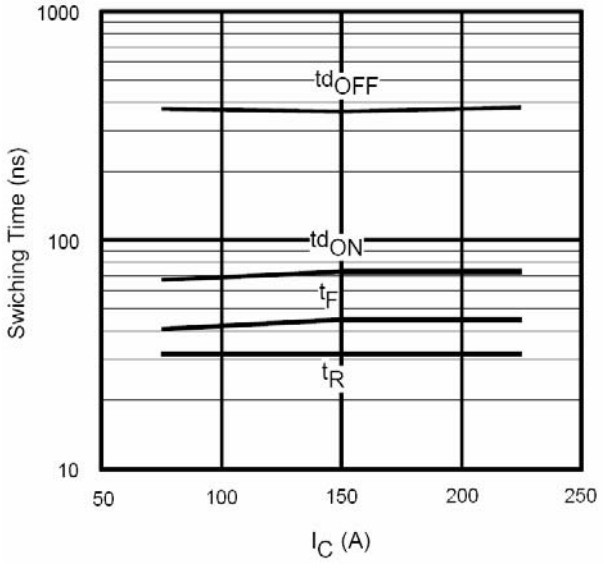


Fig 11. Typ. Switching Time vs. I_C

T_J = 125℃; L = 200μH; V_{CE} = 600V

R_G = 4.7Ω; V_{GE} = 15V

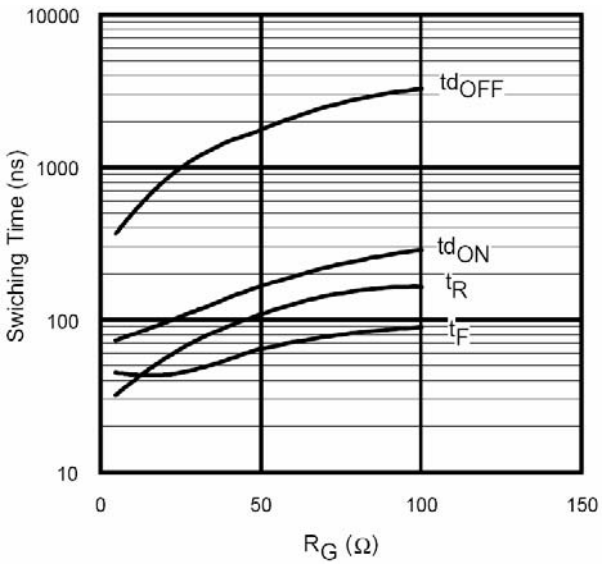


Fig 12. Typ. Switching Time vs. R_G

T_J = 125℃; L = 200μH; V_{CE} = 600V

I_{CE} = 200A; V_{GE} = 15V

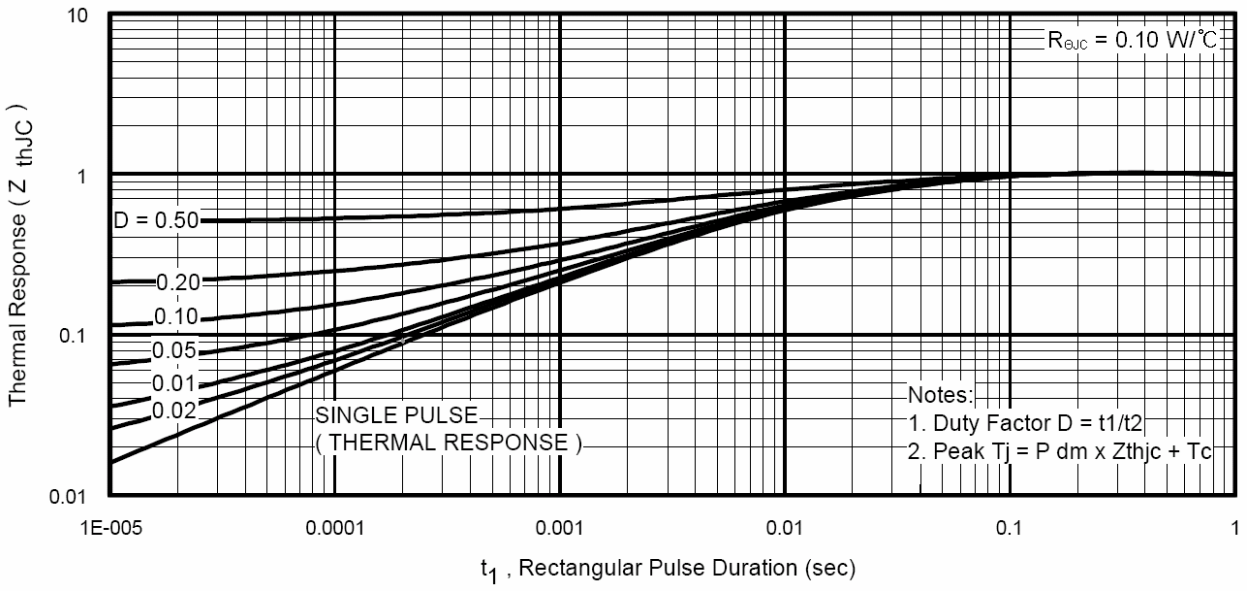


Fig 13. Normalized Transient Thermal Impedance, Juncion-to-Case (IGBT)

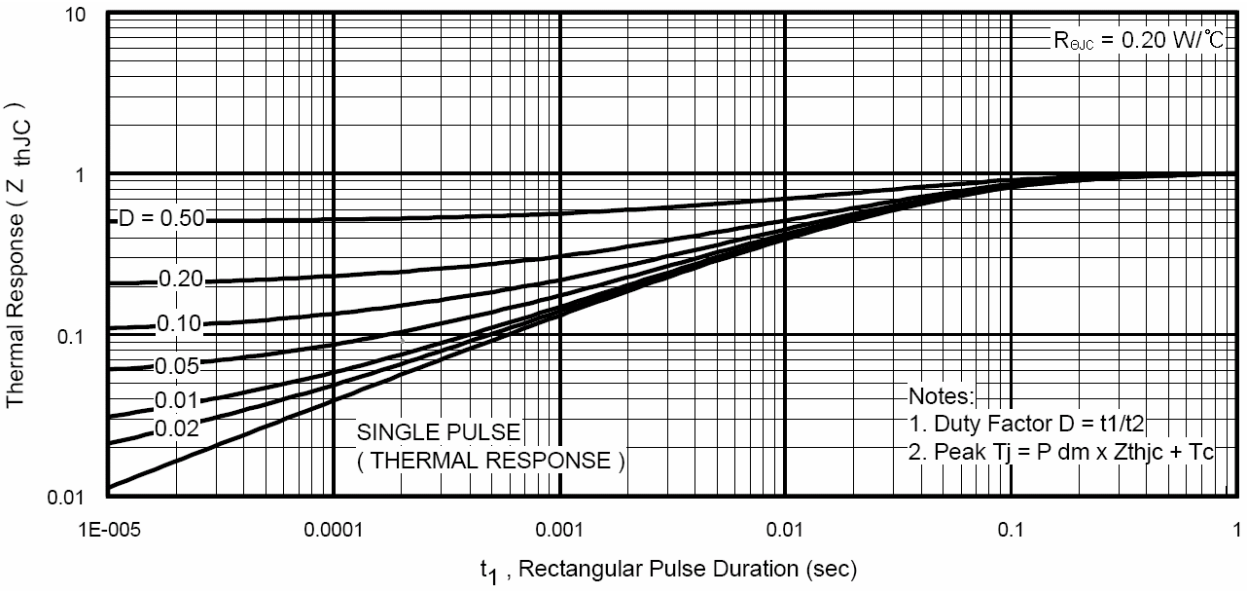
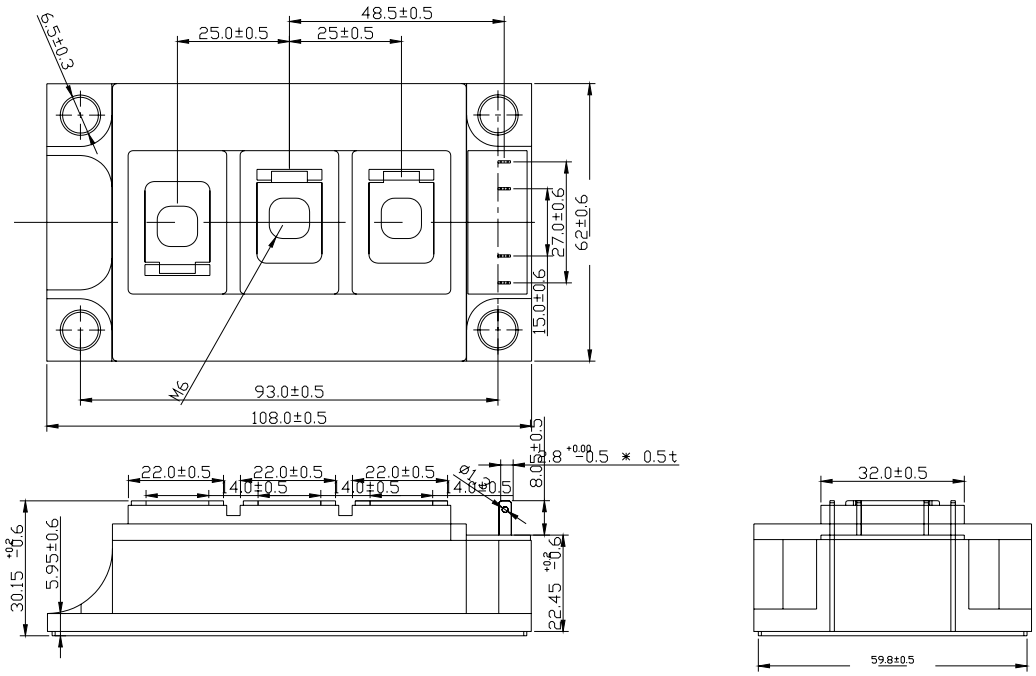


Fig 14. Normalized Transient Thermal Impedance, Juncion-to-Case (DIODE)

Package Outline (dimensions in mm)



Data and specifications subject to change without notice. May 2006